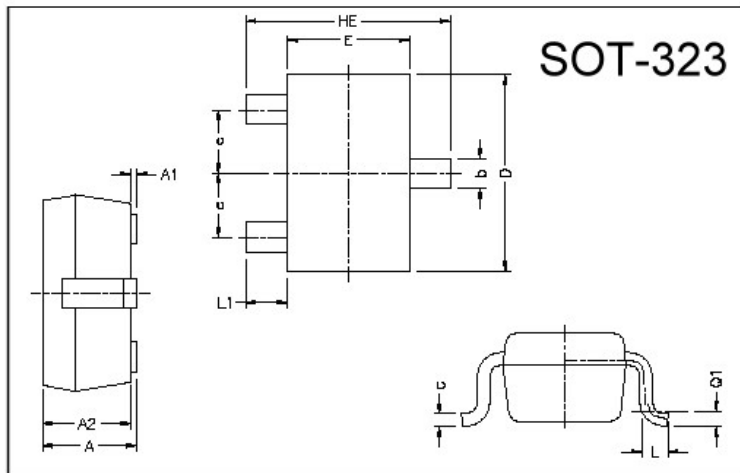


GSMBZ5221B~GSMBZ5270B

Description

ZENER DIODES

Package Dimensions

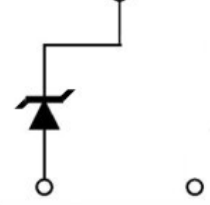


Marking :

K

A N

Circuit :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42	REF.
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65	REF.
HE	1.80	2.40	Q1	0.15	BSC.

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board Ta=25°C, Derate above 25°C	PD	225 1.8	mW mW/°C
Total Device Dissipation Alumina Substrate**TA=25°C, Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	R θ JA	417	°C/W
Junction and Storage Temperature	Tj, Tstg	-55 to +150	°C

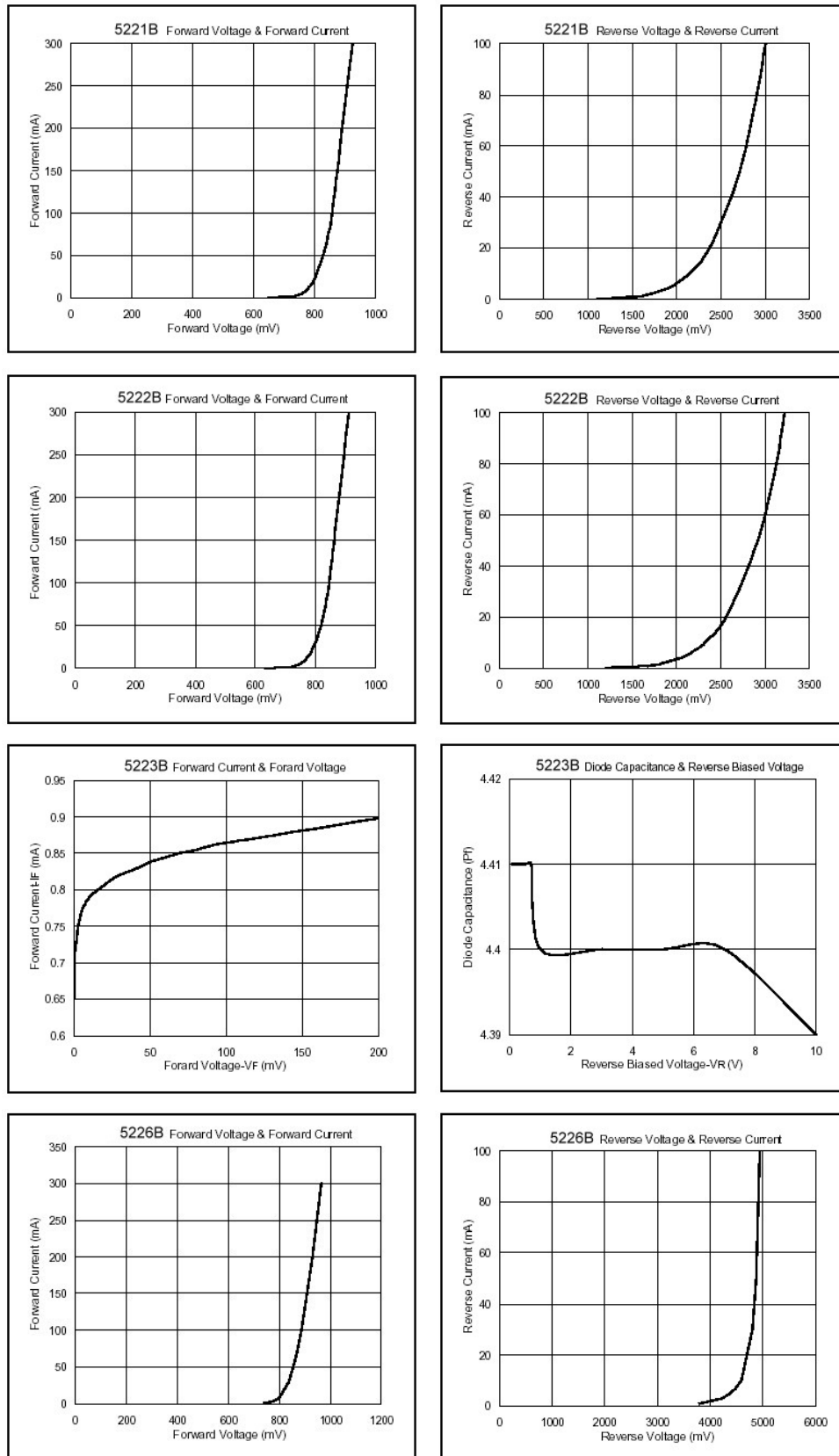
*FR-5 - 1.0 × 0.75 × 0.062 in. **Alumina-0.4 × 0.3 × 0.024 in. 99.5% alumina.

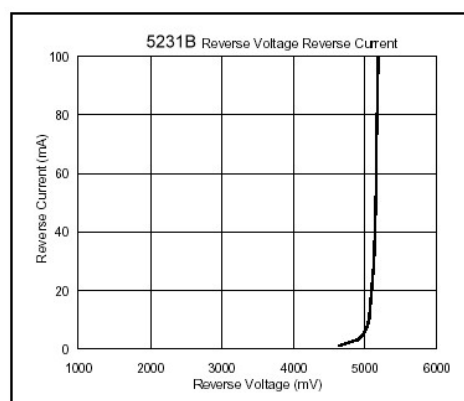
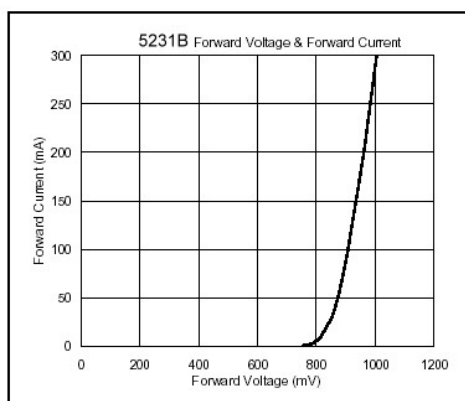
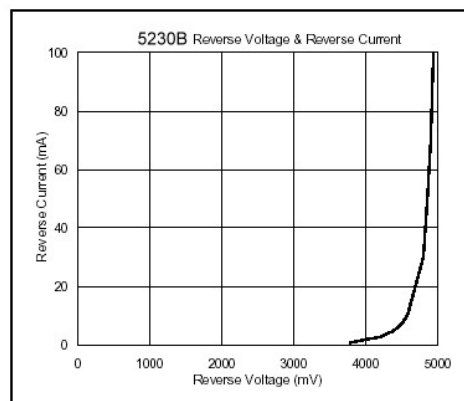
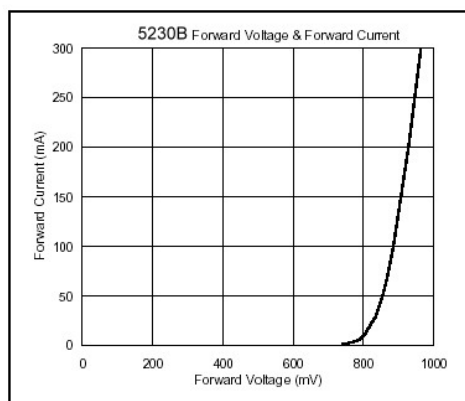
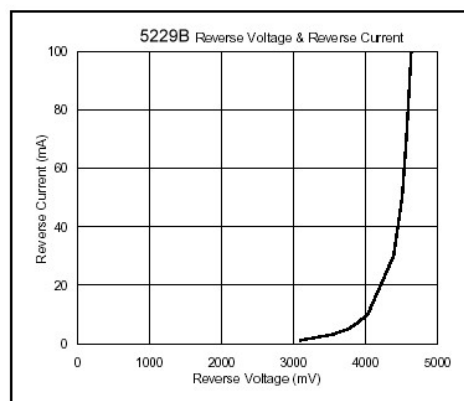
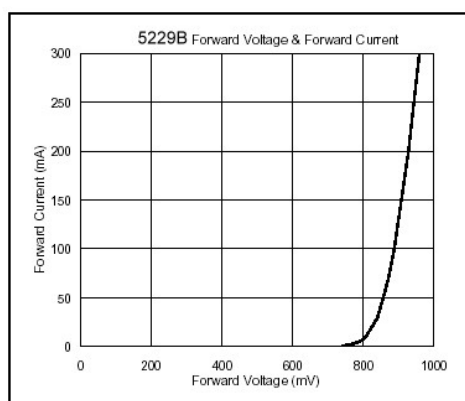
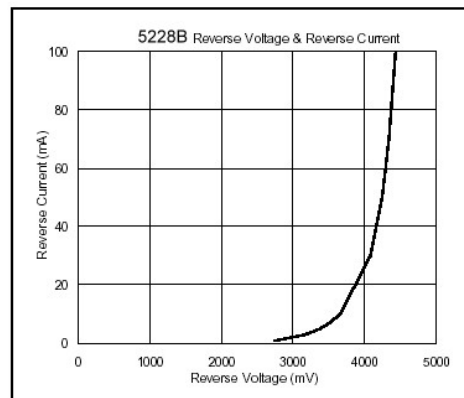
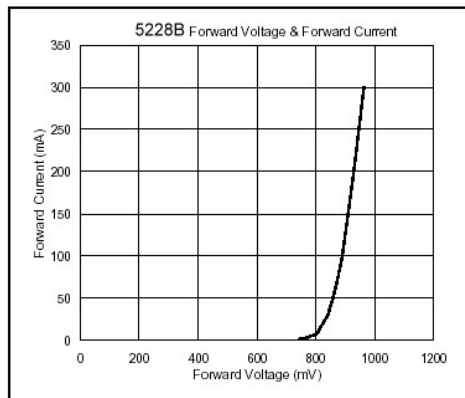
Thermal Characteristics (VF=0.9V Max @ IF=10mA for all types.)

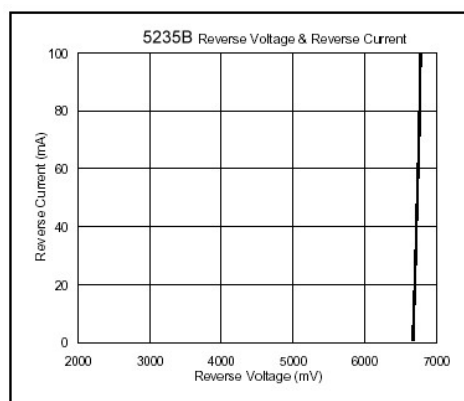
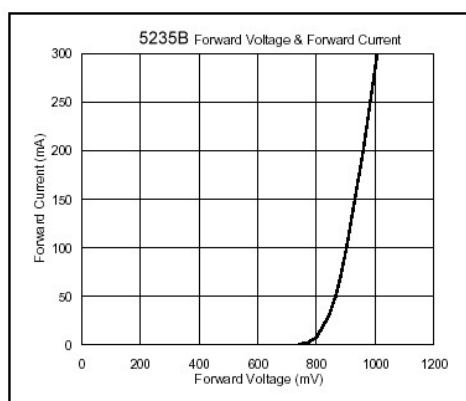
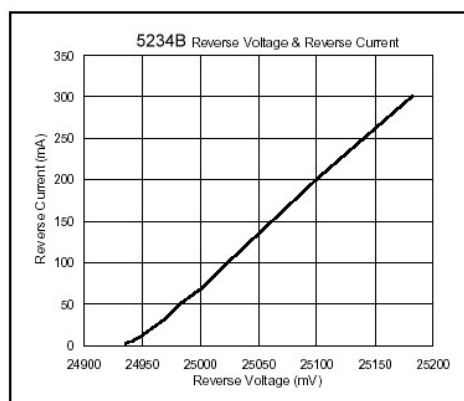
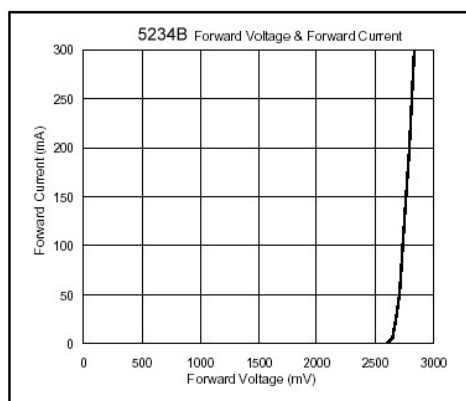
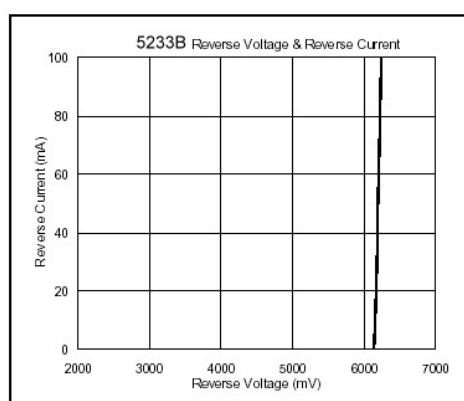
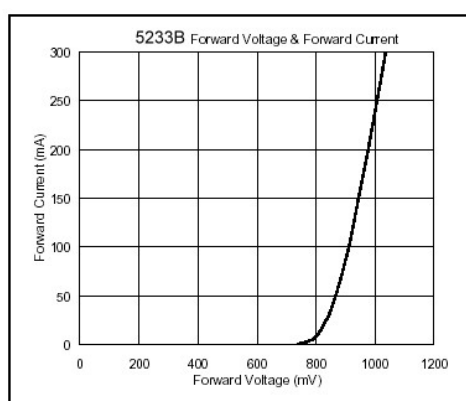
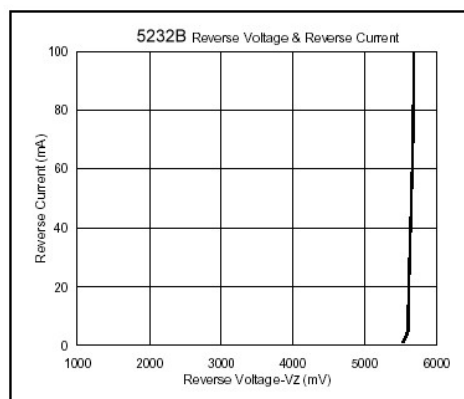
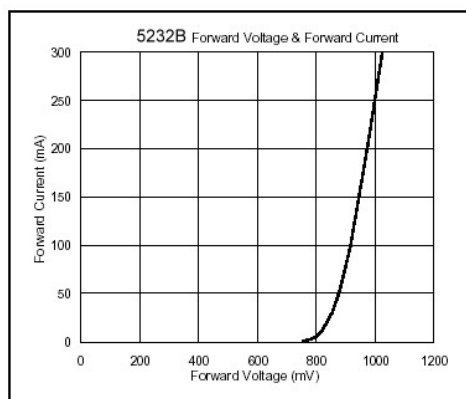
Device	Marking Code	Test Current IZT(mA)	Zener Voltage Vz(V)			ZZK IZ=0.25mA Ω Max	ZZT IZ=IZT Ω Max	Max. Reverse Current	
			Min	Nominal	Max			IR(μA)	@VR(V)
GSMBZ5221B	18A	20	2.280	2.4	2.520	1200	30	100	1.0
GSMBZ5222B	18B	20	2.375	2.5	2.625	1250	30	100	1.0
GSMBZ5223B	18C	20	2.565	2.7	2.835	1300	30	75	1.0
GSMBZ5224B	18D	20	2.660	2.8	2.940	1400	30	75	1.0
GSMBZ5225B	18E	20	2.850	3.0	3.150	1600	29	50	1.0
GSMBZ5226B	8A	20	3.135	3.3	3.465	1600	28	25	1.0
GSMBZ5227B	8B	20	3.420	3.6	3.780	1700	24	15	1.0
GSMBZ5228B	8C	20	3.705	3.9	4.095	1900	23	10	1.0
GSMBZ5229B	8D	20	4.085	4.3	4.515	2000	22	5.0	1.0
GSMBZ5230B	8E	20	4.465	4.7	4.935	1900	19	5.0	2.0
GSMBZ5231B	8F	20	4.845	5.1	5.355	1600	17	5.0	2.0
GSMBZ5232B	8G	20	5.320	5.6	5.880	1600	17	5.0	3.0
GSMBZ5233B	8H	20	5.700	6.0	6.300	1600	7.0	5.0	3.5
GSMBZ5234B	8J	20	5.890	6.2	6.510	1000	7.0	5.0	4.0
GSMBZ5235B	8K	20	6.460	6.8	7.140	750	5.0	3.0	5.0
GSMBZ5236B	8L	20	7.125	7.5	7.875	500	6.0	3.0	6.0
GSMBZ5237B	8M	20	7.790	8.2	8.610	500	8.0	3.0	6.5
GSMBZ5238B	8N	20	8.265	8.7	9.135	600	8.0	3.0	6.5
GSMBZ5239B	8P	20	8.645	9.1	9.555	600	10	3.0	7.0
GSMBZ5240B	8Q	20	9.500	10	10.500	600	17	3.0	8.0

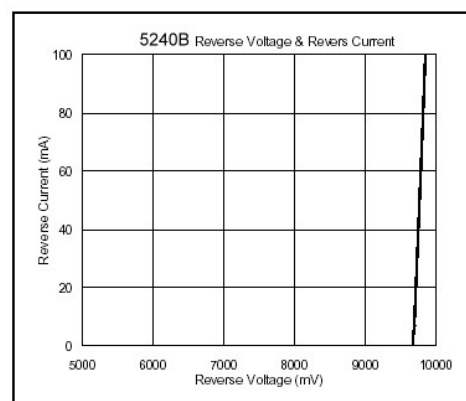
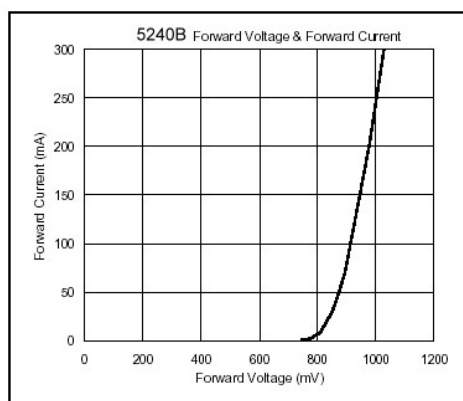
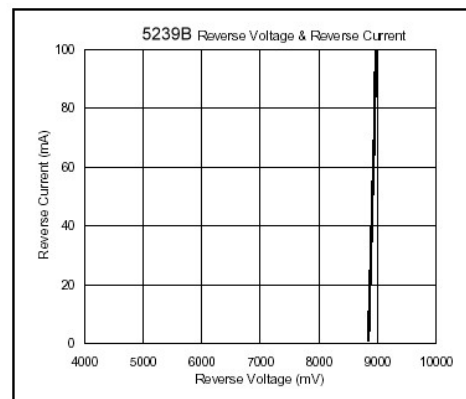
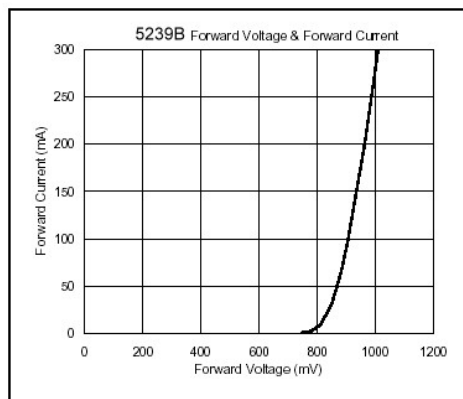
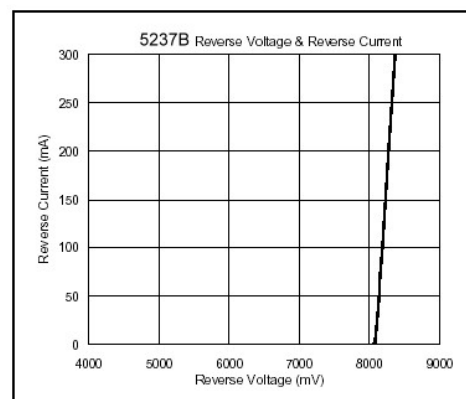
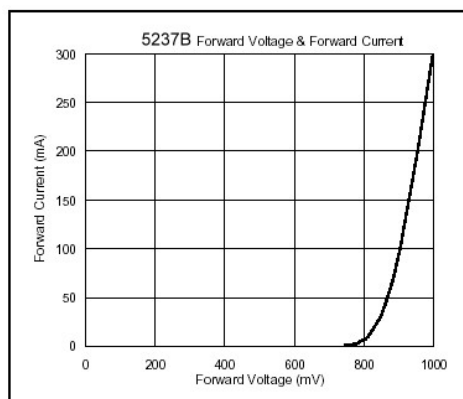
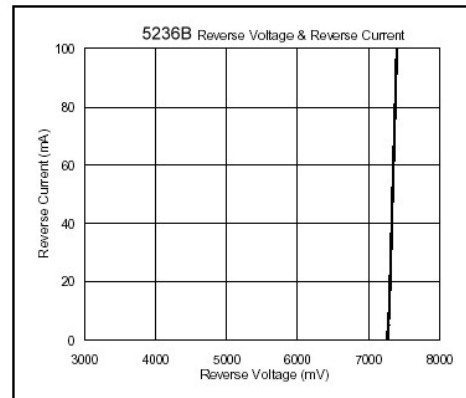
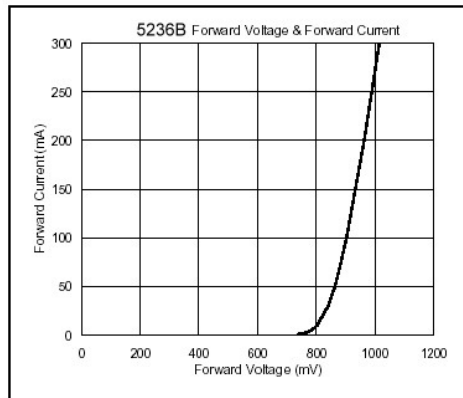
Device	Marking Code	Test Current IZT(mA)	Zener Voltage Vz(V)			ZZK IZ=0.25mA Ω Max	ZZT IZ=IZT Ω Max	Max. Reverse Current	
			Min	Nominal	Max			IR(μA)	@VR(V)
GSMBZ5241B	8R	20	10.450	11	11.550	600	22	2.0	8.4
GSMBZ5242B	8S	20	11.400	12	12.600	600	30	1.0	9.1
GSMBZ5243B	8T	9.5	12.350	13	13.650	600	13	0.5	9.9
GSMBZ5244B	8U	9.0	13.300	14	14.700	600	15	0.1	10
GSMBZ5245B	8V	8.5	14.250	15	15.750	600	16	0.1	11
GSMBZ5246B	8W	7.8	15.200	16	16.800	600	17	0.1	12
GSMBZ5247B	8X	7.4	16.150	17	17.850	600	19	0.1	13
GSMBZ5248B	8Y	7.0	17.100	18	18.900	600	21	0.1	14
GSMBZ5249B	8Z	6.6	18.050	19	19.950	600	23	0.1	14
GSMBZ5250B	81A	6.2	19.000	20	21.000	600	25	0.1	15
GSMBZ5251B	81B	5.6	20.900	22	23.100	600	29	0.1	17
GSMBZ5252B	81C	5.2	22.800	24	25.200	600	33	0.1	18
GSMBZ5253B	81D	5.0	23.750	25	26.250	600	35	0.1	19
GSMBZ5254B	81E	4.6	25.650	27	28.350	600	41	0.1	21
GSMBZ5255B	81F	4.5	26.600	28	29.400	600	44	0.1	21
GSMBZ5256B	81G	4.2	28.500	30	31.500	600	49	0.1	23
GSMBZ5257B	81H	3.8	31.350	33	34.650	700	58	0.1	25
GSMBZ5258B	81J	3.4	34.200	36	37.800	700	70	0.1	27
GSMBZ5259B	81K	3.2	37.050	39	40.950	800	80	0.1	30
GSMBZ5260B	81L	3.0	40.850	43	45.150	900	93	0.1	33
GSMBZ5261B	81M	2.7	44.650	47	49.350	1000	105	0.1	36
GSMBZ5262B	81N	2.5	48.450	51	53.550	1100	125	0.1	39
GSMBZ5263B	81P	2.2	53.200	56	58.800	1300	150	0.1	43
GSMBZ5264B	81Q	2.1	57.000	60	63.000	1400	170	0.1	46
GSMBZ5265B	81R	2.0	58.900	62	65.100	1400	185	0.1	47
GSMBZ5266B	81S	1.8	64.600	68	71.400	1600	230	0.1	52
GSMBZ5267B	81T	1.7	71.250	75	78.750	1700	270	0.1	56
GSMBZ5268B	81U	1.5	77.900	82	86.100	2000	330	0.1	62
GSMBZ5269B	81V	1.4	82.650	87	91.350	2200	370	0.1	68
GSMBZ5270B	81W	1.4	86.450	91	95.550	2300	400	0.1	69

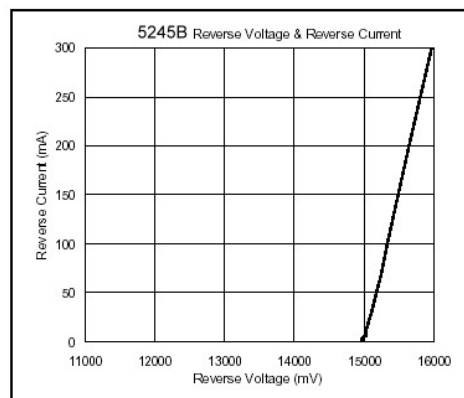
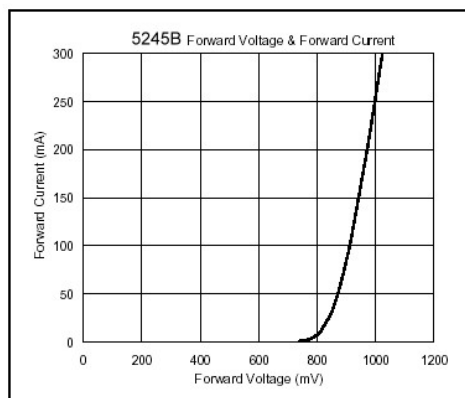
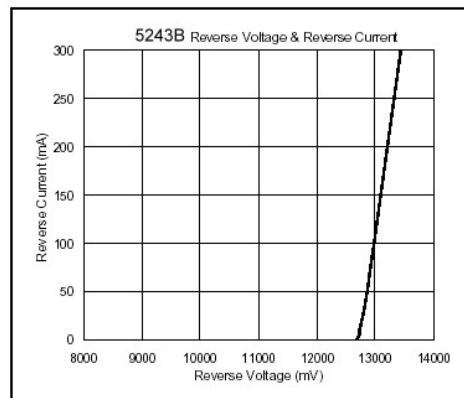
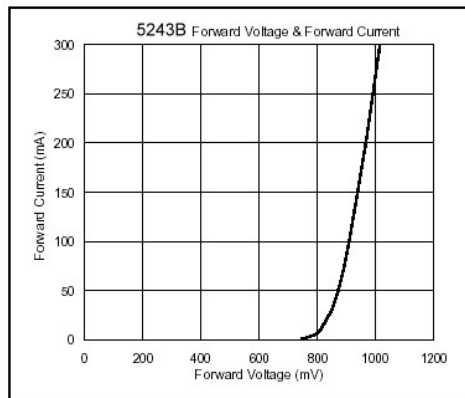
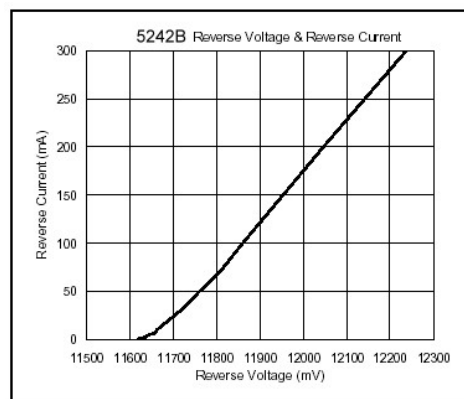
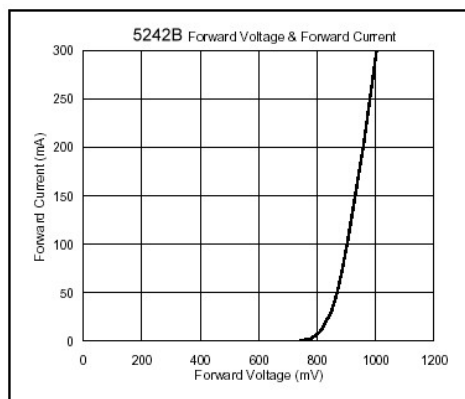
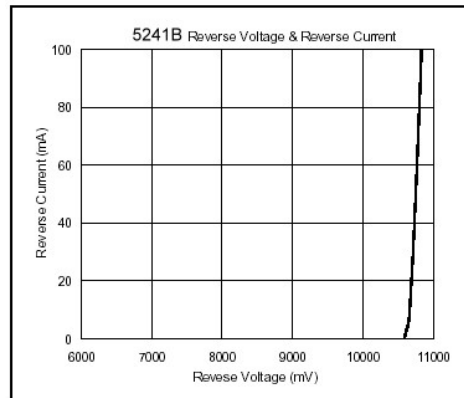
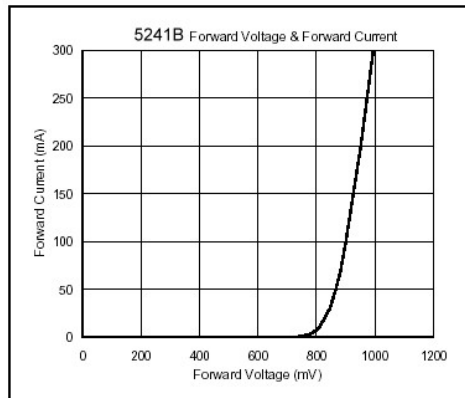
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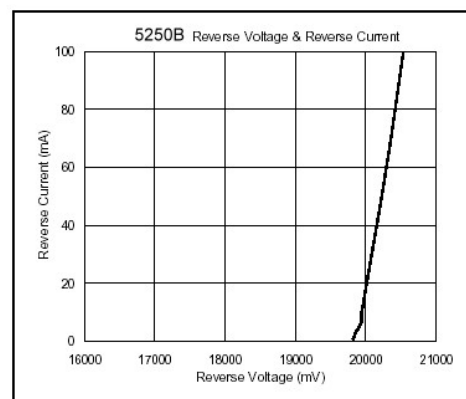
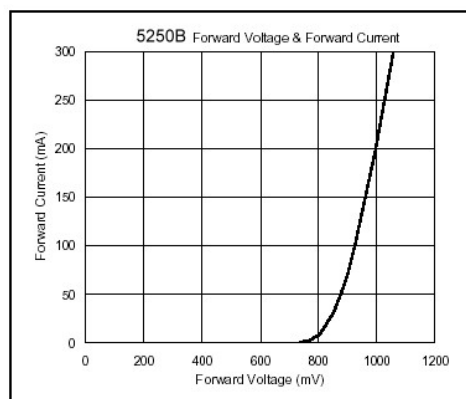
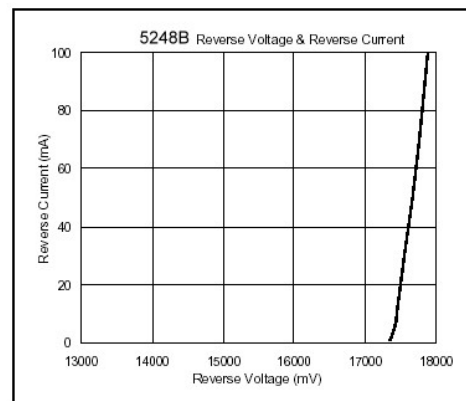
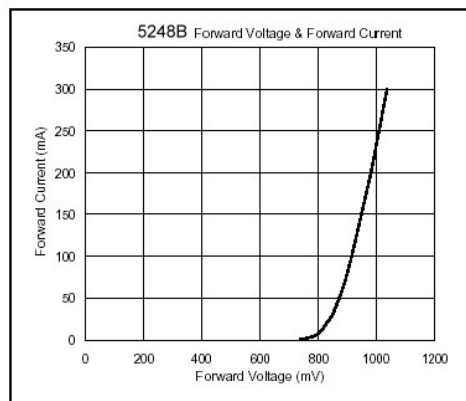
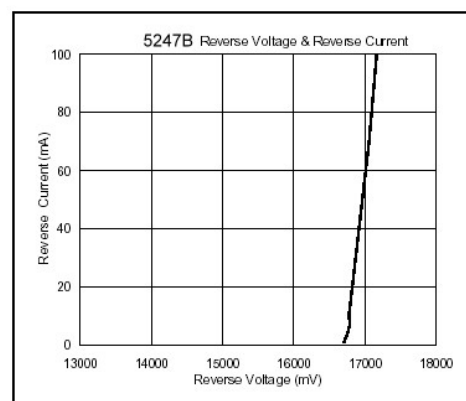
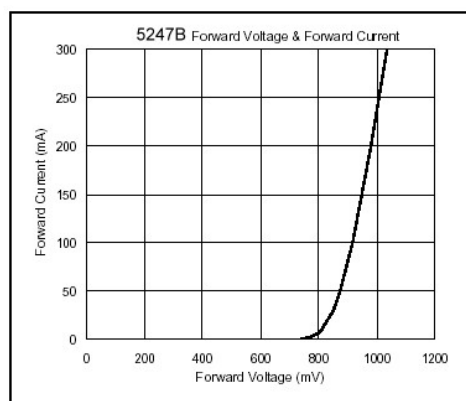
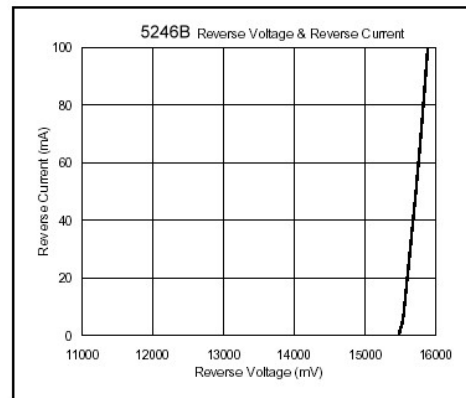
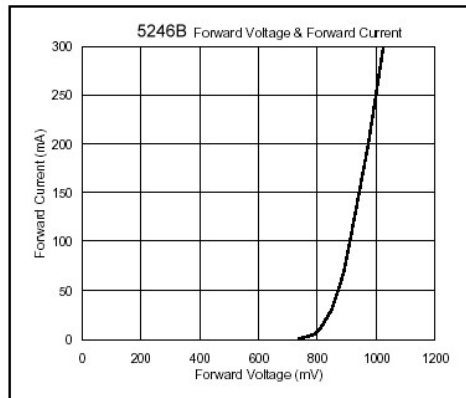


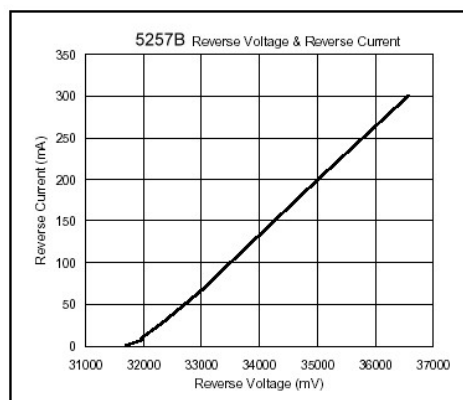
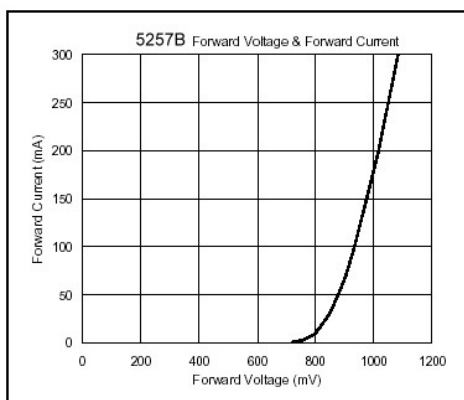
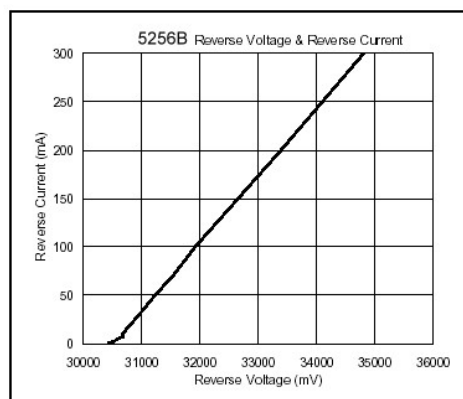
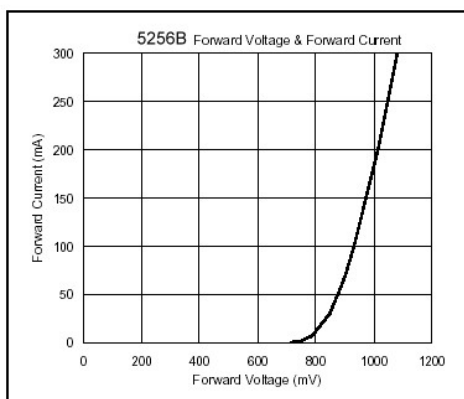
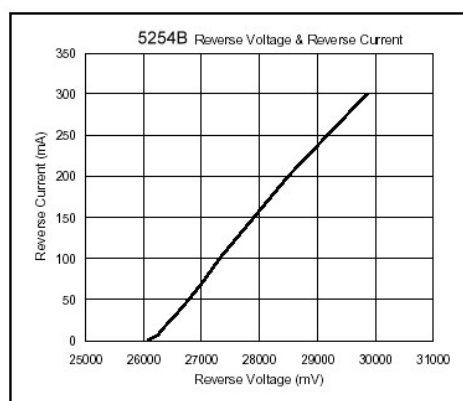
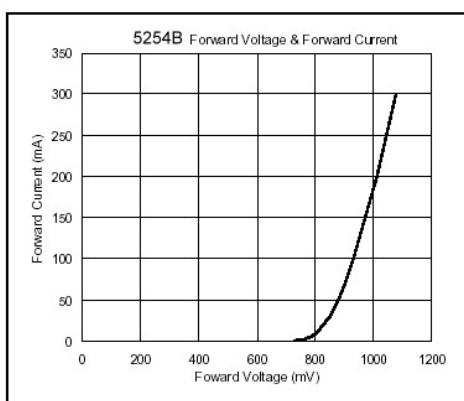
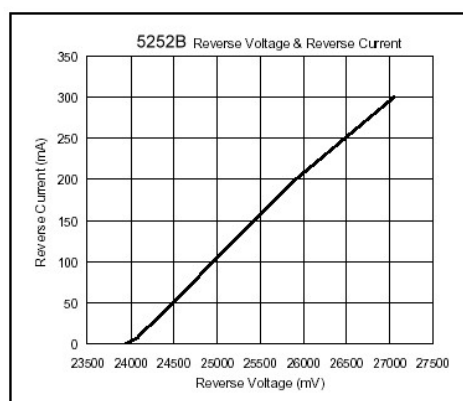
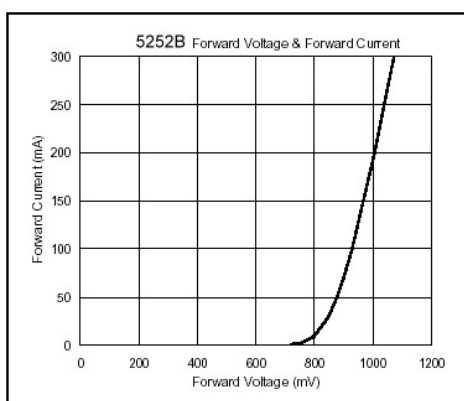










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